

2SC2334

Silicon NPN Transistors



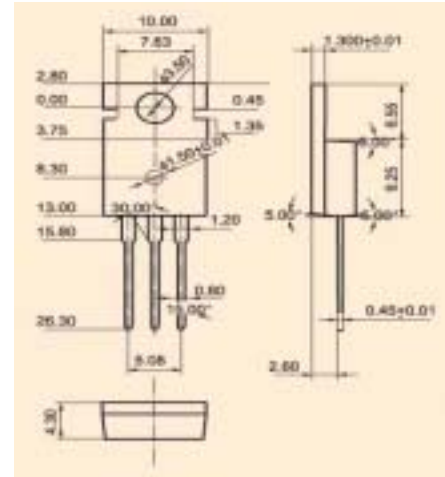
BCE

◆ Features

- . With TO-220 package
- . Complement to type 2SA1010
- . For high speed switching industrial use

◆ Absolute Maximum Ratings Tc=25°C

SYMBOL	PARAMETER	RATING	UNIT
V _{CBO}	Collector to base voltage	150	V
V _{CEO}	Collector to emitter voltage	100	V
V _{EBO}	Emitter to base voltage	7	V
I _{CP}	Peak collector current	15	A
I _C	Collector current	7	A
P _C	Collector power dissipation	40	W
T _j	Junction temperature	150	°C
T _{stg}	Storage temperature	-55~150	°C



TO-220

◆ Electrical Characteristics Tc=25°C

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
I _{CBO}	Collector-base cut-off current	V _{CB} =100V; I _E =0			10	μA
I _{EBO}	Emitter-base cut-off current	V _{EB} =5V; I _C =0			10	μA
I _{CEO}	Collector-emitter cut-off current					
V _{CBO}	Collector-base breakdown voltage					
V _{(BR)ceo}	Collector-emitter breakdown voltage	I _C =200mA; I _B =0	100			V
V _{EBO}	Emitter-base breakdown voltage					
V _{CE(sat-1)}	Collector-emitter saturation voltages	I _C =5A; I _B =0.5A			0.6	V
V _{CE(sat-2)}	Collector-emitter saturation voltages					
h _{FE-1}	Forward current transfer ratio	I _C =3A; V _{CE} =5V	40		240	
h _{FE-2}	Forward current transfer ratio	I _C =0.5A; V _{CE} =5V	40			
h _{FE-3}	Forward current transfer ratio	I _C =5A; V _{CE} =5V	20			
V _{BE(sat)1}	Base-emitter saturation voltages	I _C =5A; I _B =0.5A			1.5	V
t _{on}	Turn-on time	V _{CC} =50V I _C =5A I _{B1} =-I _{B2} =0.5A R _L =50Ω			0.5	μs
t _{stg}	Storage time				0.5	μs
t _f	Fall time				1.5	μs

◆ h_{FE-2} classification

R	O	Y
40-80	70-140	120-240